

1N4448W-Q1

List

List.....	1
Package outline.....	2
Features.....	2
Mechanical data.....	2
Maximum ratings and electrical characteristics	2
Rating and characteristic curves.....	3
Pinning information.....	4
Marking.....	4
Suggested solder pad layout.....	4
Packing information.....	5
Reel packing.....	6
Suggested thermal profiles for soldering processes.....	6
High reliability test capabilities.....	7

1N4448W-Q1

250mA Surface Mount Switching Diode-100V

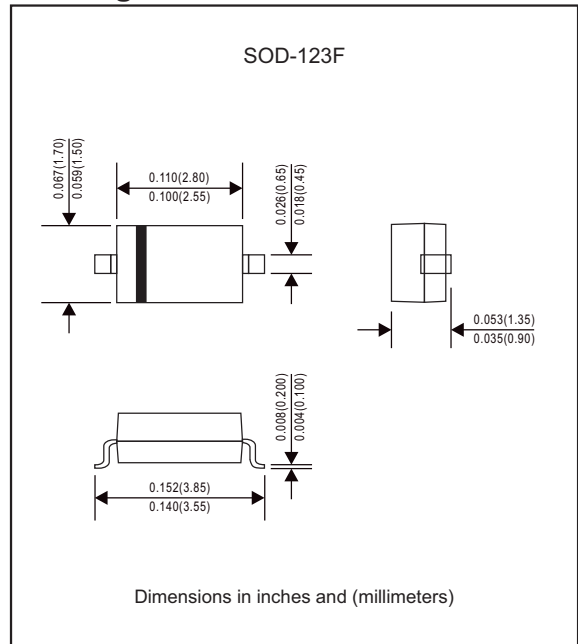
Features

- Small package
- Low reverse current
- Fast switching speed
- Surface mount package ideally suited for automatic insertion
- Silicon epitaxial planar chip
- Lead-free parts meet RoHS requirements.
- Qualified to AEC-Q101 standards for high reliability.
- Suffix "-H" indicates Halogen-free parts, ex. 1N4448W-Q1-H

Mechanical data

- Epoxy:UL94-VO rated flame retardant
- Case : Molded plastic, SOD-123F
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.010 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

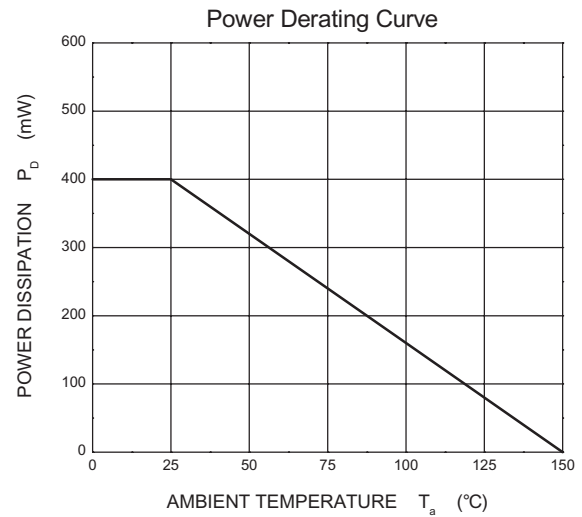
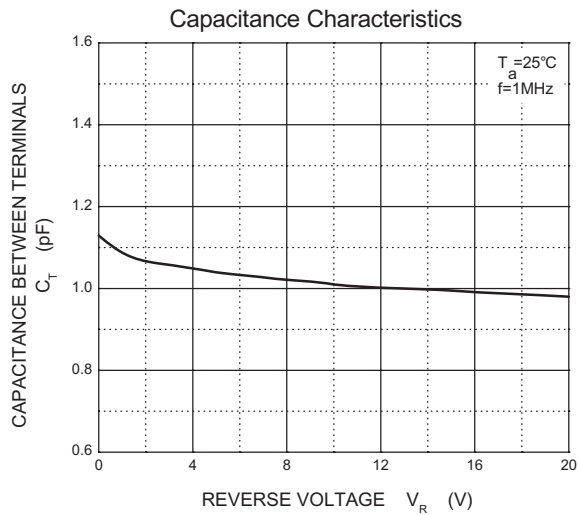
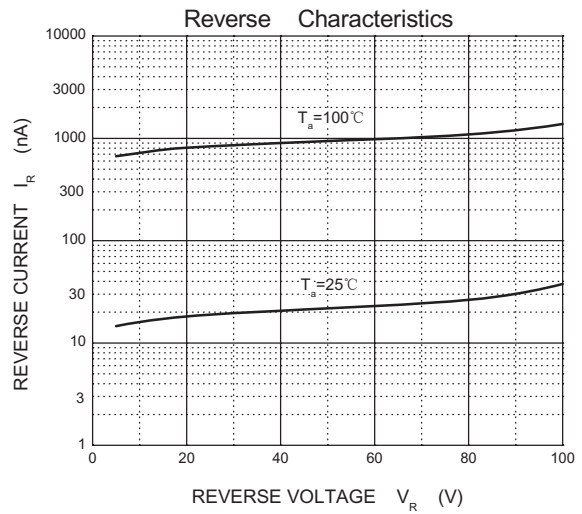
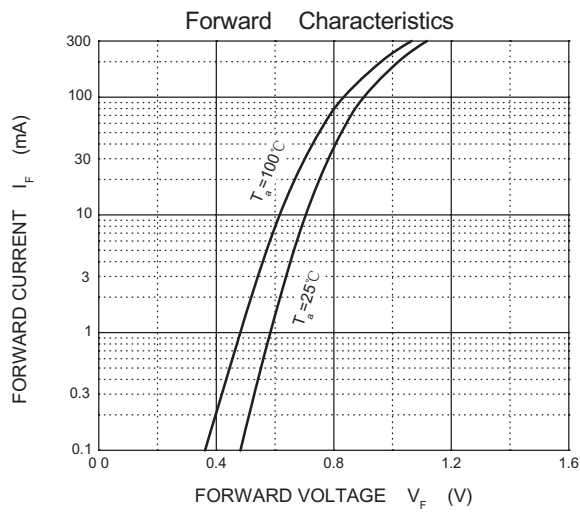
PARAMETER	Symbol	Limit	UNIT
Non-repetitive peak reverse voltage	V_{RRM}	100	V
Working peak reverse voltage DC blocking voltage	V_{RWM} V_R	80	V
Forward continuous current	I_{FM}	300	mA
Average rectified output current (note 1)	I_O	150	mA
Non-repetitive peak forward surge current 1us	I_{FSM}	4.0	A
Power dissipation (note 1)	P_D	400	mW
Typical thermal resistance junction to ambient (note 1)	$R_{\theta JA}$	250	$^{\circ}\text{C/W}$
Operating junction temperature range	T_J	-55 to +150	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITION	Symbol	MIN.	MAX.	UNIT
Reverse breakdown voltage	$I_R = 100\mu\text{A}$	$V_{(BR)R}$	80		V
Forward voltage	$I_F = 5\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 100\text{ mA}$ $I_F = 150\text{ mA}$	V_F	0.62	0.72 0.855 1.00 1.25	V
Reverse leakage current	$V_R = 80\text{V}, T_J=25^{\circ}\text{C}$ $V_R = 20\text{V}, T_J=25^{\circ}\text{C}$	I_R		0.5 25	μA nA
Capacitance between terminals	$V_R = 0\text{ V}, f = 1.0\text{MHz}$	C_T		4.0	pF
Reverse recovery time	$I_F = I_R = 10\text{mA}, I_{RR} = 0.1 \times I_R, R_L = 100\Omega$	t_{rr}		4.0	ns

Note 1: Valid provided that electrodes are kept at ambient temperature.

Rating and characteristic curves (1N4448W-Q1)



1N4448W-Q1

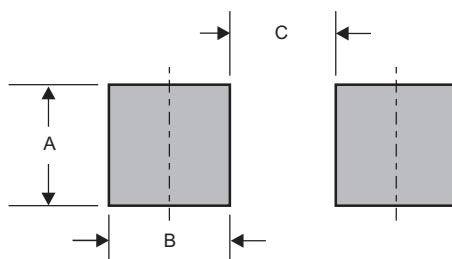
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
1N4448W-Q1	W1

Suggested solder pad layout

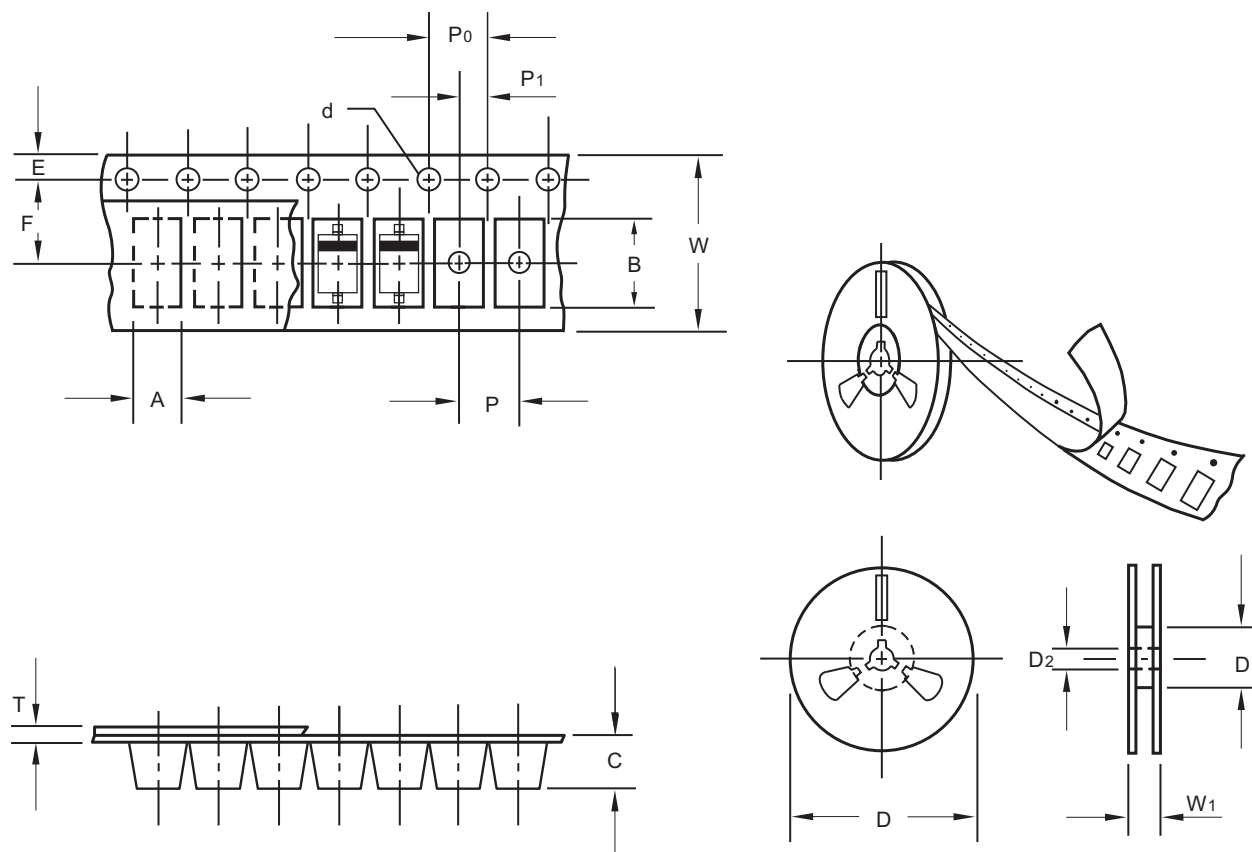


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-123F	0.048 (1.22)	0.036 (0.91)	0.093 (2.36)

1N4448W-Q1

Packing information



unit:mm

Item	Symbol	Tolerance	SOD-123F
Carrier width	A	0.1	1.85
Carrier length	B	0.1	3.95
Carrier depth	C	0.1	1.57
Sprocket hole	d	0.1	1.55
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D ₁	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	54.40
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W ₁	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

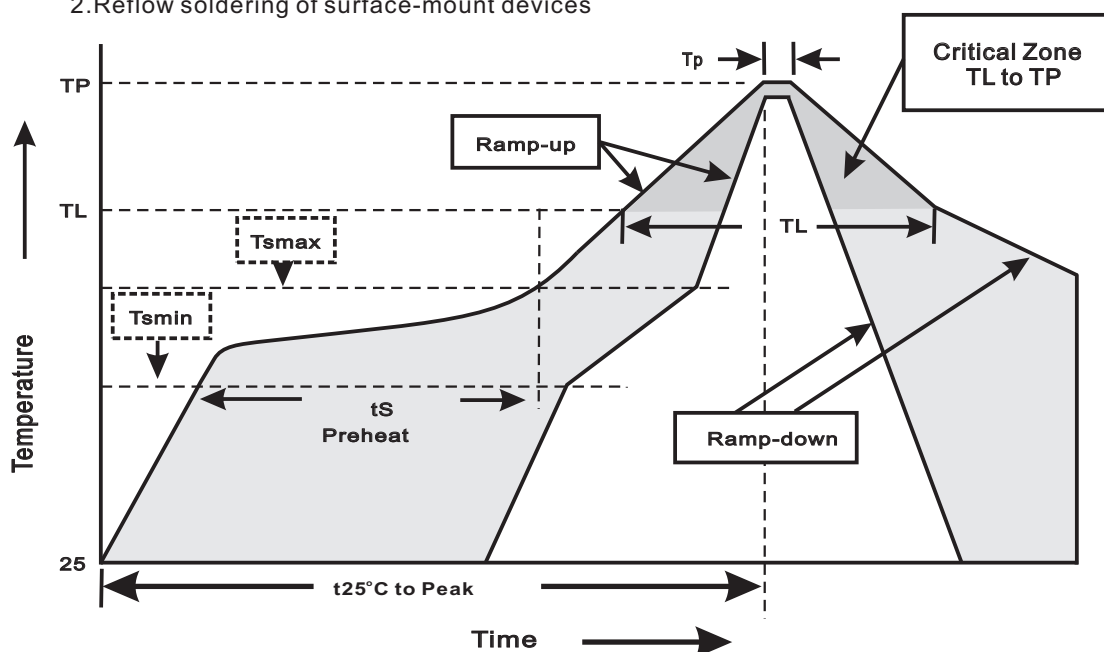
1N4448W-Q1

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-123F	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	9.5

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{Smin}) -Temperature Max(T _{Smax}) -Time(min to max)(t _S)	150°C 200°C 60~120sec
T _{Smax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

1N4448W-Q1

High reliability test capabilities

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. Operation Life	Ta=25°C , Rated Current (Io=Iomax.) Test Duration:1000hrs	MIL-STD-750E METHOD 1027.3
3. High Temperature Reverse Bias	80% Rated VR (Tj=Tjmax.)Test Duration:1000hrs	JESD22-A108
4. High Temperature Storage Life	Ta=125°C Test Duration: 1000hrs	JESD22 A-103
5. Temperature Cycle	-55°C (15min) to 150°C (15min)Test Cycles: 1000cycles	JESD22 A-104
6. Autoclave	P=2atm Ta=121°C RH=100% Test Duration:96hrs	JESD22 A-102
7. Intermittent Operational Life	Ta=25°C, On/Io Max. 2min, Off/2min, Test Cycles:15000cycles	MIL-STD-750E METHOD 1037
8. Solderability	245±5°C for 5sec	J-STD-002
9. Moisture Resistance	Ta=85°C/85% Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
10. Resistance To Solder Heat	260±5°C for 10sec	JESD22 B-106
11. High Temperature High Humidity Reverse Bias	Ta=85°C, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101